

TECHNICAL DATA

SL74LV244

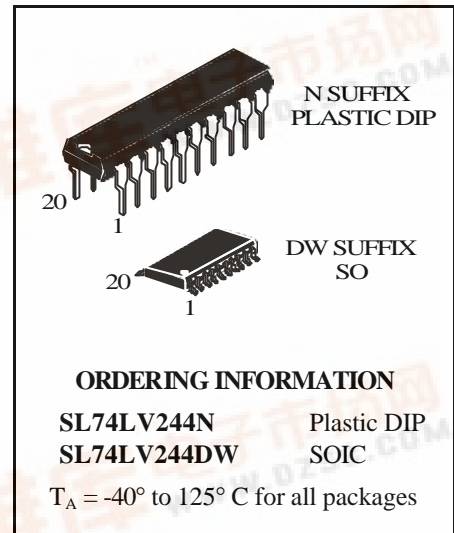
OCTAL BUFFER/LINE DRIVE; 3-STATE

The SL74LV244 is a low-voltage Si-gate CMOS device and is pin and function compatible with SL74HC/HCT244.

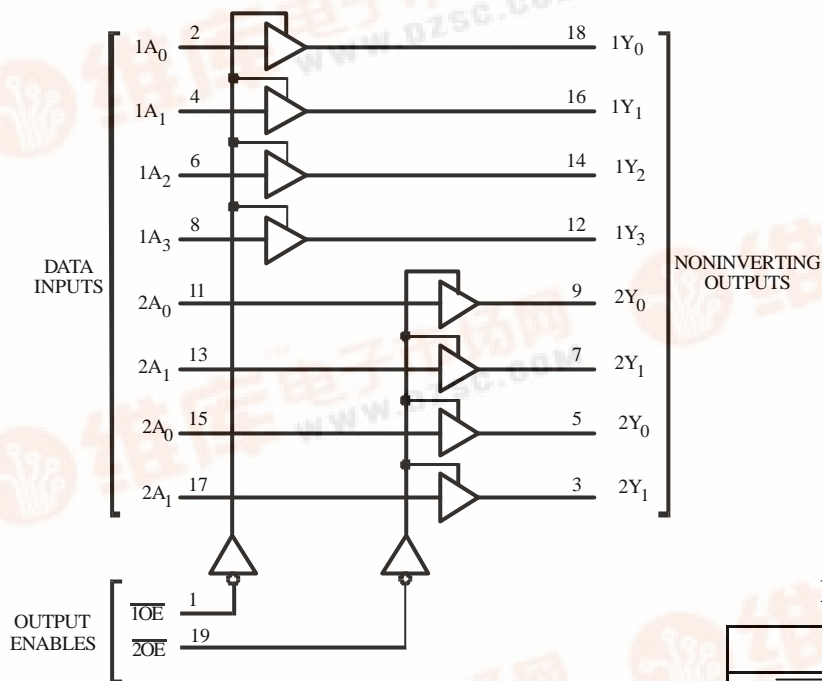
The SL74LV244 is an octal non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs IOE and 2OE. A HIGH on nOE causes the outputs to assume a high impedance OFF-state.

The SL74LV244 is identical to the SL74LV240 but has non-inverting outputs.

- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 1.2 to 3.6 V
- Low Input Current: 1.0 μ A, 0.1 μ A at $\dot{O} = 25^\circ\text{N}$
- Output Current: 8 mA at $V_{CC} = 3.0$ V
- High Noise Immunity Characteristic of CMOS Devices



LOGIC DIAGRAM



PIN ASSIGNMENT

IOE	1	20	V_{CC}
1A ₀	2	19	2OE
2Y ₃	3	18	1Y ₀
1A ₁	4	17	2A ₃
2Y ₂	5	16	1Y ₁
1A ₂	6	15	2A ₂
2Y ₁	7	14	1Y ₂
1A ₃	8	13	2A ₁
2Y ₀	9	12	1Y ₃
GND	10	11	2A ₀

FUNCTION TABLE

Input		Output
nOE	nAn	nYn
L	L	L
L	H	H
H	X	Z

H= high level
L = low level
X = don't care
Z = high impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC supply voltage	-0.5 to +5.0	V
I _{IK} * ¹	DC Input diode current	±20	mA
I _{OK} * ²	DC Output diode current	±50	mA
I _O * ³	DC Output source or sink current	±35	mA
I _{CC}	DC V _{CC} current	±70	mA
I _{GND}	DC GND current	±70	mA
P _D	Power dissipation per package: * ⁴ Plastic DIP SO	750 500	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1.5 mm (Plastic DIP Package), 0.3 mm (SO Package) from Case for 4 Seconds	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

*¹ V_I < -0.5 V or V_I > V_{CC} + 0.5 V.

*² V_O < -0.5 V or V_O > V_{CC} + 0.5 V.

*³ -0.5 V < V_O < V_{CC} + 0.5 V.

*⁴ Derating - Plastic DIP: - 12 mW/°C from 70° to 125°C
SO Package: : - 8 mW/°C from 70° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	1.2	3.6	V
V _I	Input Voltage	0	V _{CC}	V
V _O	Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)			ns
	V _{CC} = 1.2 V	0	1000	
	V _{CC} = 2.0 V	0	700	
	V _{CC} = 3.0 V	0	500	
	V _{CC} = 3.6 V	0	400	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND ≤ (V_{IN} or V_{OUT}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test conditions	V _{CC} V	Guaranteed Limit						Unit
				25° C		-40° C to 85° C		125° C		
				min	max	min	max	min	max	
V _{IH}	HIGH level input voltage		1.2	0.9	-	0.9	-	0.9	-	V
			2.0	1.4	-	1.4	-	1.4	-	
			3.0	2.1	-	2.1	-	2.1	-	
			3.6	2.5	-	2.5	-	2.5	-	
V _{IL}	LOW level input voltage		1.2	-	0.3	-	0.3	-	0.3	V
			2.0	-	0.6	-	0.6	-	0.6	
			3.0	-	0.9	-	0.9	-	0.9	
			3.6	-	1.1	-	1.1	-	1.1	
V _{OH}	HIGH level output voltage	V _I = V _{IH} or V _{IL} I _O = -50 μA	1.2	1.1	-	1.0	-	1.0	-	V
			2.0	1.92	-	1.9	-	1.9	-	
			3.0	2.92	-	2.9	-	2.9	-	
			3.6	3.52	-	3.5	-	3.5	-	
			V _I = V _{IH} or V _{IL} I _O = -8 mA	3.0	2.48	-	2.34	-	2.20	-
V _{OL}	LOW level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 μA	1.2	-	0.09	-	0.1	-	0.1	V
			2.0	-	0.09	-	0.1	-	0.1	
			3.0	-	0.09	-	0.1	-	0.1	
			3.6	-	0.09	-	0.1	-	0.1	
			V _I = V _{IH} or V _{IL} I _O = 8 mA	3.0	-	0.33	-	0.4	-	0.5
I _I	Input current	V _I = V _{CC} or 0 V	*	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	Three state leakage current	3-state outputs V _I (01,19) = V _{IH} V _O = V _{CC} or 0 V	1.2 *	-	±0.5	-	±5	-	±10	μA
I _{CC}	Supply current	V _I = V _{CC} or 0 V I _O = 0 μA	*	-	8.0	-	80	-	160	μA

* V_{CC} = 3.3 ± 0.3 V

AC ELECTRICAL CHARACTERISTICS (C_L=50 pF, t_r=t_f=6.0 ns)

Symbol	Parameter	Test conditions	V _{CC} V	Guaranteed Limit						Unit
				25 °C		-40 °C to 85 °C		125 °C		
				min	max	min	max	min	max	
t _{PHL} , t _{PLH}	Propagation delay, 1An to 1Yn, 2An to 2Yn	V _I = 0 V or V _{CC} Figure 1 and 3	1.2	-	100	-	125	-	150	ns
			2.0	-	24	-	30	-	36	
			*	-	15	-	19	-	23	
t _{PHZ} , t _{PLZ}	Propagation delay, 1OE to 1Yn, 2OE to 2Yn	V _I = 0 V or V _{CC} Figure 2 and 4	1.2	-	140	-	175	-	210	ns
			2.0	-	30	-	35	-	41	
			*	-	20	-	24	-	28	
t _{PZH} , t _{PZL}	Propagation delay, 1OE to 1Yn, 2OE to 2Yn	V _I = 0 V or V _{CC} Figure 2 and 4	1.2	-	140	-	175	-	210	ns
			2.0	-	32	-	40	-	48	
			*	-	20	-	25	-	30	
t _{THL} , t _{TLH}	Output Transition Time, Any Output	V _I = 0 V or V _{CC} Figure 1 and 3	1.2	-	60	-	75	-	90	ns
			2.0	-	16	-	20	-	24	
			*	-	10	-	13	-	15	
C _I	Input capacitance		3.0	-	7.0	-	7.0	-	7.0	pF
C _{PD}	Power dissipation capacitance (per one channel)	V _I = 0 V or V _{CC}		-	50	-	-	-	-	pF

* V_{CC} = 3.3 ± 0.3 V

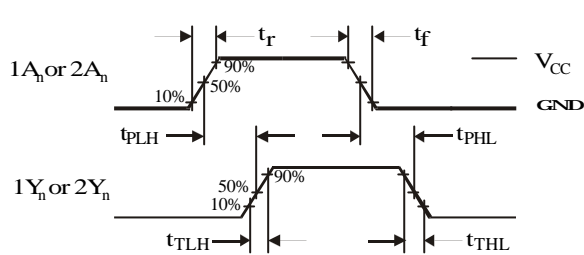


Figure 1. Switching Waveforms

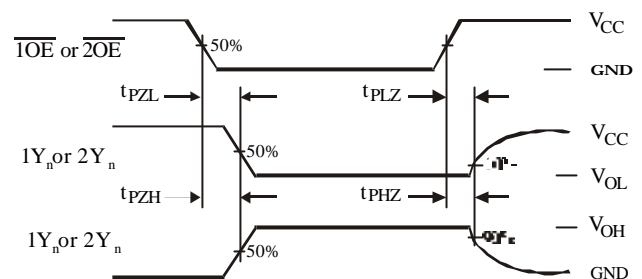
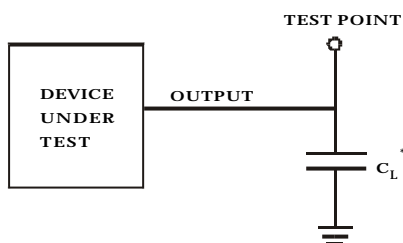
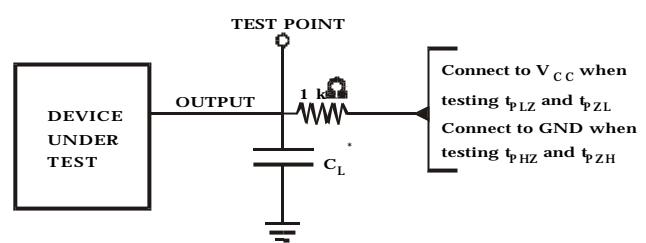


Figure 2. Switching Waveforms



* Includes all probe and jig capacitance

Figure 3. Test Circuit



* Includes all probe and jig capacitance

Figure 4. Test Circuit